Tadeusz Suski

List of Publications by Year in Descending Order

305 papers	8,183 citations	41 h-index	80 g-index
344 ext. papers	8,707 ext. citations	2.5 avg, IF	5.05 L-index

#	Paper	IF	Citations
305	Structural and emission improvement of cyan-emitting InGaN quantum wells by introducing a large substrate misorientation angle. *Optical Materials Express*, **2022**, 12, 119	2.6	1
304	Band gap tuning in InxGa1-xN/InyGa1-yN short period superlattices. *Superlattices and Microstructures*, **2021**, 155, 106907	2.8	2
303	Influence of substrate misorientation on the emission and waveguiding properties of a blue (In,Al,Ga)N laser-like structure studied by synchrotron radiation microbeam X-ray diffraction. *Photonics Research*, **2021**, 9, 299	6	3
302	Quantum-confined Stark effect and mechanisms of its screening in InGaN/GaN light-emitting diodes with a tunnel junction. *Optics Express*, **2021**, 29, 1824-1837	3.3	7
301	Hydrostatic pressure dependence of indirect and direct excitons in InGaN/GaN quantum wells. *Physical Review B*, **2020**, 101,	3.3	2
300	Above 25 nm emission wavelength shift in blue-violet InGaN quantum wells induced by GaN substrate misorientation profiling: towards broad-band superluminescent diodes. *Optics Express*, **2020**, 28, 22524-22539	3.3	3
299	InGaN blue light emitting micro-diodes with current path defined by tunnel junction. *Optics Letters*, **2020**, 45, 4332-4335	3	1
298	Nitride light-emitting diodes for cryogenic temperatures. *Optics Express*, **2020**, 28, 30299-30308	3.3	3
297	First-Principles Calculation of Bandgaps of Al1−xInxN Alloys and Short-Period Al1−xInxN/Al1−yInyN Superlattices. *Physica Status Solidi (B): Basic Research*, **2020**, 257, 1900530	1.3	3
296	Thermal conductivity of thin films of gallium nitride, doped with aluminium, measured with 3ω method. *Solid State Sciences*, **2020**, 101, 106105	3.4	5
295	ReviewReview on Optimization and Current Status of (Al,In)GaN Superluminescent Diodes. *ECS Journal of Solid State Science and Technology*, **2020**, 9, 015010	2	6
294	Direct observation of long distance lateral transport in InGaN/GaN quantum wells. *Journal of Applied Physics*, **2019**, 125, 055702	2.5	
293	Impact of the substrate lattice constant on the emission properties of InGaN/GaN short-period superlattices grown by plasma assisted MBE. *Superlattices and Microstructures*, **2019**, 133, 106209	2.8	3
292	Beyond Quantum Efficiency Limitations Originating from the Piezoelectric Polarization in Light-Emitting Devices. *ACS Photonics*, **2019**, 6, 1963-1971	6.3	16
291	Screening of quantum-confined Stark effect in nitride laser diodes and superluminescent diodes. *Applied Physics Express*, **2019**, 12, 044001	2.4	7
290	Theoretical study of nitride short period superlattices. *Journal of Physics Condensed Matter*, **2018**, 30, 063001	1.8	20
289	Compositional and strain analysis of In(Ga)N/GaN short period superlattices. *Journal of Applied Physics*, **2018**, 123, 024304	2.5	8

288	Role of the electron blocking layer in the graded-index separate confinement heterostructure nitride laser diodes. *Superlattices and Microstructures*, **2018**, 116, 114-121	2.8	2
287	450 nm (Al,In)GaN optical amplifier with double 'j-shape' waveguide for master oscillator power amplifier systems. *Optics Express*, **2018**, 26, 7351-7357	3.3	10
286	Switching of exciton character in double InGaN/GaN quantum wells. *Physical Review B*, **2018**, 98,	3.3	8
285	Influence of hydrogen pre-growth flow on indium incorporation into InGaN layers. *Journal of Crystal Growth*, **2017**, 464, 123-126	1.6	2
284	AlGaInN laser-diode technology for optical clocks and atom interferometry **2017**,		4
283	Comparison of wurtzite GaN/AlN and ZnO/MgO short-period superlattices: Calculation of band gaps and built-in electric field. *Physica Status Solidi (B): Basic Research*, **2017**, 254, 1600704	1.3	11
282	Lateral grating DFB AlGaInN laser diodes for optical communications and atomic clocks.. *Journal of Physics: Conference Series*, **2017**, 810, 012053	0.3	1
281	Monolithic cyan violet InGaN/GaN LED array. *Physica Status Solidi (A) Applications and Materials Science*, **2017**, 214, 1600815	1.6	6
280	Bandgap behavior of InGaN/GaN short period superlattices grown by metal-organic vapor phase epitaxy. *Physica Status Solidi (B): Basic Research*, **2017**, 254, 1600710	1.3	7
279	Theoretical study of the composition pulling effect in InGaN metalorganic vapor-phase epitaxy growth. *Japanese Journal of Applied Physics*, **2017**, 56, 078003	1.4	20
278	Band gap engineering of In(Ga)N/GaN short period superlattices. *Scientific Reports*, **2017**, 7, 16055	4.9	16
277	AlGaInN diode-laser technology for optical clocks and atom interferometry. *Journal of Physics: Conference Series*, **2017**, 810, 012052	0.3	1
276	AlGaInN laser diode bars for high-power, optical integration and quantum technologies **2017**,		1
275	GaN laser diodes for quantum technologies **2017**,		1
274	Tapered waveguide high power AlGaInN laser diodes and amplifiers for optical integration and quantum technologies **2017**,		2
273	Band gaps and built-in electric fields in InAlN/GaN short period superlattices: Comparison with (InAlGa)N quaternary alloys. *Physical Review B*, **2016**, 93,	3.3	9
272	High speed visible light communication using blue GaN laser diodes **2016**,		6
271	Free-space and underwater GHz data transmission using AlGaInN laser diode technology **2016**,		2

270	Photoluminescence of InGaN/GaN quantum wells grown on c-plane substrates with locally variable miscut. *Physica Status Solidi (B): Basic Research*, **2016**, 253, 284-291	1.3	6
269	AlGaInN laser diode technology for systems applications **2016**,		2
268	A Model of Radiative Recombination in (In,Al,Ga)N/GaN Structures with Significant Potential Fluctuations. *Acta Physica Polonica A*, **2016**, 130, 1209-1212	0.6	0
267	Structural and electronic properties of wurtzite MgZnO and BeMgZnO alloys and their thermodynamic stability. *Journal of Applied Physics*, **2016**, 120, 215704	2.5	12
266	Nitride superluminescent diodes with broadened emission spectrum fabricated using laterally patterned substrate. *Optics Express*, **2016**, 24, 9673-82	3.3	17
265	Properties of InGaN/GaN multiquantum wells grown on semipolar (20-21) substrates with different miscuts. *Journal of Crystal Growth*, **2015**, 423, 28-33	1.6	2
264	Negative-T0 InGaN laser diodes and their degradation. *Applied Physics Letters*, **2015**, 106, 171107	3.4	7
263	Influence of internal electric fields on band gaps in short period GaN/GaAlN and InGaN/GaN polar superlattices. *Journal of Applied Physics*, **2015**, 118, 075702	2.5	17
262	Thermal conductivity of donor-doped GaN measured with 3ω and stationary methods. *Low Temperature Physics*, **2015**, 41, 563-566	0.7	1
261	Influence of strain and internal electric fields on band gaps in short period nitride based superlattices. *Superlattices and Microstructures*, **2015**, 82, 438-446	2.8	10
260	Thermal conductivity of heavily doped bulk crystals GaN:O. Free carriers contribution. *Materials Research Express*, **2015**, 2, 085902	1.7	24
259	Effect of hydrogen during growth of quantum barriers on the properties of InGaN quantum wells. *Journal of Crystal Growth*, **2015**, 414, 38-41	1.6	20
258	Influence of quantum well inhomogeneities on absorption, spontaneous emission, photoluminescence decay time, and lasing in polar InGaN quantum wells emitting in the blue-green spectral region. *Applied Physics A: Materials Science and Processing*, **2014**, 115, 1015-1023	2.6	6
257	True-blue laser diodes grown by plasma-assisted MBE on bulk GaN substrates. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2014**, 11, 666-669		1
256	Short period polar and nonpolar m InN/n GaN superlattices. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2014**, 11, 678-681		2
255	XPS method as a useful tool for studies of quantum well epitaxial materials: Chemical composition and thermal stability of InGaN/GaN multilayers. *Journal of Alloys and Compounds*, **2014**, 597, 181-187	5.7	3
254	Revealing of the transition from n- to p-type conduction of InN:Mg by photoconductivity effect measurement. *Scientific Reports*, **2014**, 4, 4371	4.9	19
253	Band gaps and internal electric fields in semipolar short period InN/GaN superlattices. *Applied Physics Letters*, **2014**, 104, 232101	3.4	4

252	The discrepancies between theory and experiment in the optical emission of monolayer In(Ga)N quantum wells revisited by transmission electron microscopy. *Applied Physics Letters*, **2014**, 104, 182103	3.4	41
251	Advantage of In- over N-polarity for disclosure of p-type conduction in InN:Mg. *Journal of Applied Physics*, **2014**, 115, 173704	2.5	3
250	Nitride-based laser diodes and superluminescent diodes. *Photonics Letters of Poland*, **2014**, 6,	2.1	2
249	Photoluminescence and pressure effects in short period InN/nGaN superlattices. *Journal of Applied Physics*, **2013**, 113, 123101	2.5	25
248	Peculiarities in the pressure dependence of photoluminescence in InAlN. *Physica Status Solidi (B): Basic Research*, **2013**, 250, 677-682	1.3	3
247	InGaN laser diodes with reduced AlGaN cladding thickness fabricated on GaN plasmonic substrate. *Applied Physics Letters*, **2013**, 102, 151102	3.4	11
246	High optical power ultraviolet superluminescent InGaN diodes **2013**,		2
245	Graded-index separate confinement heterostructure InGaN laser diodes. *Applied Physics Letters*, **2013**, 103, 261107	3.4	24
244	Band gaps in InN/GaN superlattices: Nonpolar and polar growth directions. *Journal of Applied Physics*, **2013**, 114, 223102	2.5	12
243	Temperature-Dependence of Exciton Radiative Recombination in (Al,Ga)N/GaN Quantum Wells Grown ona-Plane GaN Substrates. *Japanese Journal of Applied Physics*, **2013**, 52, 08JC01	1.4	8
242	Pressure studies of multicarrier conduction in undoped InN grown on GaN buffer. *Physica Status Solidi (B): Basic Research*, **2013**, 250, 746-749	1.3	1
241	Hydrostatic pressure and strain effects in short period InN/GaN superlattices. *Applied Physics Letters*, **2012**, 101, 092104	3.4	22
240	Universal behavior of photoluminescence in GaN-based quantum wells under hydrostatic pressure governed by built-in electric field. *Journal of Applied Physics*, **2012**, 112, 053509	2.5	13
239	Thermal carrier emission and nonradiative recombinations in nonpolar (Al,Ga)N/GaN quantum wells grown on bulk GaN. *Journal of Applied Physics*, **2012**, 111, 033517	2.5	10
238	GaN substrates with variable vicinal angles for laser diode applications **2012**,		2
237	Band Structure and Quantum Confined Stark Effect in InN/GaN superlattices. *Crystal Growth and Design*, **2012**, 12, 3521-3525	3.5	36
236	Unambiguous relationship between photoluminescence energy and its pressure evolution in InGaN/GaN quantum wells. *Physica Status Solidi (B): Basic Research*, **2012**, 249, 476-479	1.3	1
235	Influence of GaN substrate off-cut on properties of InGaN and AlGaN layers. *Crystal Research and Technology*, **2012**, 47, 321-328	1.3	28

234	InGaN tapered laser diodes. *Electronics Letters*, **2012**, 48, 1232	1.1	3
233	Lateral Control of Indium Content and Wavelength of III-Nitride Diode Lasers by Means of GaN Substrate Patterning. *Applied Physics Express*, **2012**, 5, 021001	2.4	21
232	Cavity suppression in nitride based superluminescent diodes. *Journal of Applied Physics*, **2012**, 111, 083106	2.5	27
231	Nonlinear emission properties of an optically anisotropic GaN-based microcavity. *Physical Review B*, **2012**, 86,	3.3	5
230	Coexistence of free holes and electrons in InN:Mg with In- and N-growth polarities. *Journal of Applied Physics*, **2012**, 111, 093719	2.5	7
229	Band gap bowing in quaternary nitride semiconducting alloys. *Applied Physics Letters*, **2011**, 98, 241905	3.4	26
228	Optically pumped 500 nm InGaN green lasers grown by plasma-assisted molecular beam epitaxy. *Journal of Applied Physics*, **2011**, 110, 063110	2.5	39
227	Different behavior of semipolar and polar InGaN/GaN quantum wells: Pressure studies of photoluminescence. *Physica Status Solidi (A) Applications and Materials Science*, **2011**, 208, 1526-1528	1.6	3
226	Indium incorporation into InGaN and InAlN layers grown by metalorganic vapor phase epitaxy. *Journal of Crystal Growth*, **2011**, 318, 496-499	1.6	32
225	Band gap bowings and anomalous pressure effects in III-V nitride alloys: Role of In-segregation. *Physica Status Solidi (A) Applications and Materials Science*, **2011**, 208, 1558-1561	1.6	5
224	InGaN mini-laser diode arrays with cw output power of 500 mW. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 2348-2350		2
223	Theoretical simulations of radiative recombination time in polar InGaN quantum wells. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 2273-2275		3
222	Highly reproducible, stable and multiply regenerated surface-enhanced Raman scattering substrate for biomedical applications. *Journal of Materials Chemistry*, **2011**, 21, 8662		59
221	Tailoring the light-matter coupling in anisotropic microcavities: Redistribution of oscillator strength in strained m-plane GaN/AlGaN quantum wells. *Physical Review B*, **2011**, 84,	3.3	13
220	Size effects in band gap bowing in nitride semiconducting alloys. *Physical Review B*, **2011**, 83,	3.3	27
219	Intrinsic dynamics of weakly and strongly confined excitons in nonpolar nitride-based heterostructures. *Physical Review B*, **2011**, 83,	3.3	26
218	Secondary ions mass spectroscopy measurements of dopant impurities in highly stressed InGaN laser diodes. *Applied Physics Letters*, **2011**, 98, 241115	3.4	12
217	Deep Levels in GaN p-n Junctions Studied by Deep Level Transient Spectroscopy and Laplace Transform Deep-Level Spectroscopy. *Acta Physica Polonica A*, **2011**, 119, 669-671	0.6	6

216	InAlGaN laser diodes grown by plasma assisted molecular beam epitaxy. *Lithuanian Journal of Physics*, **2011**, 51, 276-282	1.1	0
215	Interplay between Internal and External Electric Field Studied by Photoluminescence in InGaN/GaN Light Emitting Diodes. *Acta Physica Polonica A*, **2011**, 120, 891-893	0.6	
214	Limitations to band gap tuning in nitride semiconductor alloys. *Applied Physics Letters*, **2010**, 96, 101907	3.4	37
213	Hole carrier concentration and photoluminescence in magnesium doped InGaN and GaN grown on sapphire and GaN misoriented substrates. *Journal of Applied Physics*, **2010**, 108, 023516	2.5	14
212	Anomalous composition dependence of the band gap pressure coefficients in In-containing nitride semiconductors. *Physical Review B*, **2010**, 81,	3.3	26
211	Temperature dependence of superluminescence in InGaN-based superluminescent light emitting diode structures. *Journal of Applied Physics*, **2010**, 108, 013110	2.5	17
210	Tilt of InGaN layers on miscut GaN substrates. *Physica Status Solidi - Rapid Research Letters*, **2010**, 4, 142-144	2.5	9
209	In-clustering effects in InAlN and InGaN revealed by high pressure studies. *Physica Status Solidi (A) Applications and Materials Science*, **2010**, 207, 1369-1371	1.6	13
208	In-clustering induced anomalous behavior of band gap in InAlN and InGaN. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2010**, 7, 1283-1286		7
207	Interplay of stimulated emission and Auger-like effect in violet and blue InGaN laser diodes. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2010**, 7, 1835-1837		
206	Effect of efficiency droop in violet and blue InGaN laser diodes. *Applied Physics Letters*, **2009**, 95, 071108	3.4	19
205	Different pressure behavior of GaN/AlGaN quantum structures grown along polar and nonpolar crystallographic directions. *Journal of Applied Physics*, **2009**, 105, 063104	2.5	19
204	Search for free holes in InN:Mg-interplay between surface layer and Mg-acceptor doped interior. *Journal of Applied Physics*, **2009**, 105, 123713	2.5	25
203	Fast measurements of photoreflectance spectra by using multi-channel detector. *Physica Status Solidi (A) Applications and Materials Science*, **2009**, 206, 847-850	1.6	6
202	Photoreflectance spectroscopy of the band bending and the energy gap for Mg-doped InN layers. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2009**, 6, S739-S742		2
201	What is new in nitride laser diodes reliability studies. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2009**, 6, S881-S884		
200	Gap bowing in Inx Ga1−x N and Inx Al1−x N under pressure. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2009**, 6, S368-S371		7
199	Carrier recombination under one-photon and two-photon excitation in GaN epilayers. *Micron*, **2009**, 40, 118-21	2.3	2

198	Deep level transient spectroscopy signatures of majority traps in GaN p□ diodes grown by metal-organic vapor-phase epitaxy technique on GaN substrates. *Physica B: Condensed Matter*, **2009** , 404, 4889-4891	2.8	17
197	Influence of indium clustering on the band structure of semiconducting ternary and quaternary nitride alloys. *Physical Review B*, **2009**, 80,	3.3	123
196	Nitride laser diode arrays **2009**,		2
195	Why InGaN laser-diode degradation is accompanied by the improvement of its thermal stability **2008**,		7
194	Photoreflectance of InN and InN:Mg layers: An evidence of Fermi level shift toward the valence band upon Mg doping in InN. *Applied Physics Letters*, **2008**, 93, 131917	3.4	16
193	Bowing of the band gap pressure coefficient in InxGa1□N alloys. *Journal of Applied Physics*, **2008**, 103, 033514	2.5	48
192	Electronic structure and effective masses of InN under pressure. *Journal of Applied Physics*, **2008**, 104, 013704	2.5	25
191	Carrier recombination mechanisms in nitride single quantum well light-emitting diodes revealed by photo- and electroluminescence. *Journal of Applied Physics*, **2008**, 104, 094504	2.5	3
190	Substrate misorientation induced strong increase in the hole concentration in Mg doped GaN grown by metalorganic vapor phase epitaxy. *Applied Physics Letters*, **2008**, 93, 172117	3.4	26
189	Pressure-induced piezoelectric effects in near-lattice-matched GaN/AlInN quantum wells. *Journal of Applied Physics*, **2008**, 104, 063505	2.5	9
188	Built-in electric field and large Stokes shift in near-lattice-matched GaN□AlInN quantum wells. *Applied Physics Letters*, **2008**, 92, 201901	3.4	19
187	Influence of substrate misorientation on properties of InGaN layers grown on freestanding GaN. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2008**, 5, 1485-1487		11
186	Conduction band filling in In-rich InGaN and InN under hydrostatic pressure. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2008**, 5, 1488-1490		1
185	Optically pumped lasing of GaN/AlGaN structures grown along a non-polar crystallographic direction. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2008**, 5, 2173-2175		
184	Band structure and effective mass of InN under pressure. *Physica Status Solidi (B): Basic Research*, **2008**, 245, 887-889	1.3	3
183	Fabrication and properties of GaN-based lasers. *Journal of Crystal Growth*, **2008**, 310, 3979-3982	1.6	10
182	LASER DIODES GROWN ON BULK GALLIUM NITRIDE SUBSTRATES **2008**, 223-252		
181	The influence of alloy disorder and hydrostatic pressure on electrical and optical properties of In-rich InGaN compounds **2007**,		7

180	Modelling the growth of nitrides in ammonia-rich environment. *Crystal Research and Technology*, **2007**, 42, 1281-1290	1.3	10
179	Thermal analysis of InGaN/GaN (GaN substrate) laser diodes using transient interferometric mapping. *Microelectronics Reliability*, **2007**, 47, 1649-1652	1.2	1
178	Optical gain and saturation behavior in homoepitaxially grown InGaN/GaN/AlGaN laser structures. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2007**, 4, 82-85		
177	Investigation of polarization-induced electric field screening in InGaN light emitting diodes by means of hydrostatic pressure. *Physica Status Solidi (B): Basic Research*, **2007**, 244, 32-37	1.3	3
176	High pressure studies of radiative recombination mechanisms in InN. *Physica Status Solidi (B): Basic Research*, **2007**, 244, 38-41	1.3	3
175	Role of localized donor states in transport and photoluminescence of InN revealed by hydrostatic pressure studies. *Physica Status Solidi (B): Basic Research*, **2007**, 244, 1825-1828	1.3	3
174	Gain mechanisms in field-free InGaN layers grown on sapphire and bulk GaN substrate. *Physica Status Solidi - Rapid Research Letters*, **2007**, 1, 141-143	2.5	3
173	Towards identification of localized donor states in InN. *Semiconductor Science and Technology*, **2007**, 22, 1161-1164	1.8	3
172	Comparison of gain in group-III-nitride laser structures grown by metalorganic vapour phase epitaxy and plasma-assisted molecular beam epitaxy on bulk GaN substrates. *Semiconductor Science and Technology*, **2007**, 22, 736-741	1.8	3
171	Optically pumped GaN/AlGaN separate-confinement heterostructure laser grown along the (11$\bar{2}$0) nonpolar direction. *Applied Physics Letters*, **2007**, 90, 081104	3.4	14
170	Role of the electron blocking layer in the low-temperature collapse of electroluminescence in nitride light-emitting diodes. *Applied Physics Letters*, **2007**, 90, 103507	3.4	44
169	Correlation between luminescence and compositional striations in InGaN layers grown on miscut GaN substrates. *Applied Physics Letters*, **2007**, 91, 211904	3.4	35
168	Role of conduction-band filling in the dependence of InN photoluminescence on hydrostatic pressure. *Physical Review B*, **2007**, 76,	3.3	27
167	Mode dynamics of high power (InAl)GaN based laser diodes grown on bulk GaN substrate. *Journal of Applied Physics*, **2007**, 101, 083109	2.5	12
166	Tunable broad-area InGaN laser diodes in external cavity **2007**,		2
165	Optically Pumped Laser Action on Nitride Based Separate Confinement Heterostructures Grown along the (11$\bar{2}$0) Crystallographic Direction. *Acta Physica Polonica A*, **2007**, 112, 467-472	0.6	
164	Strong electric field and nonuniformity effects in GaN/AlN quantum dots revealed by high pressure studies. *Applied Physics Letters*, **2006**, 89, 051902	3.4	6
163	Carrier recombination and diffusion in GaN revealed by transient luminescence under one-photon and two-photon excitations. *Applied Physics Letters*, **2006**, 89, 172119	3.4	17

162	Degradation mechanisms in InGaN laser diodes grown on bulk GaN crystals. *Applied Physics Letters*, **2006**, 88, 201111	3.4	64
161	Band-to-band character of photoluminescence from InN and In-rich InGaN revealed by hydrostatic pressure studies. *Applied Physics Letters*, **2006**, 89, 121915	3.4	13
160	Effect of high-temperature annealing on the residual strain and bending of freestanding GaN films grown by hydride vapor phase epitaxy. *Applied Physics Letters*, **2006**, 88, 141909	3.4	27
159	Anomalous temperature characteristics of single wide quantum well InGaN laser diode. *Applied Physics Letters*, **2006**, 88, 071121	3.4	19
158	Hydrostatic pressure dependence of polarization-induced interface charge in AlGaN□GaN heterostructures determined by means of capacitance-voltage characterization. *Journal of Applied Physics*, **2006**, 100, 113712	2.5	4
157	Broad-area high-power CW operated InGaN laser diodes **2006**, 6133, 168		5
156	High-Pressure Crystallization of GaN **2006**, 1-43		
155	Barrier-to-well carrier dynamics of InGaN/GaN multi-quantum-wells grown by plasma assisted MBE on bulk GaN substrates. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2006**, 3, 1962-1965		1
154	Screening of polarization induced electric fields in blue/violet InGaN/GaN laser diodes by Si doping in quantum barriers revealed by hydrostatic pressure. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2006**, 3, 2303-2306		3
153	Bending in HVPE GaN free-standing films: effects of laser lift-off, polishing and high-pressure annealing. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2006**, 3, 1475-1478		3
152	Optical properties of InGaN/GaN quantum wells on sapphire and bulk GaN substrate. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2006**, 3, 2078-2081		1
151	Towards identification of degradation mechanisms in InGaN laser diodes grown on bulk GaN crystals. *Physica Status Solidi (A) Applications and Materials Science*, **2006**, 203, 1778-1782	1.6	4
150	Dissociation of V_{Ga}□N complexes in HVPE GaN by high pressure and high temperature annealing. *Physica Status Solidi (B): Basic Research*, **2006**, 243, 1436-1440	1.3	7
149	Role of band potential roughness on the luminescence properties of InGaN quantum wells grown by MBE on bulk GaN substrates. *Physica Status Solidi (B): Basic Research*, **2006**, 243, 1614-1618	1.3	6
148	Localized donor state above the conduction band minimum in InN revealed by high pressure and temperature transport experiments. *Physica Status Solidi (B): Basic Research*, **2006**, 243, 1537-1540	1.3	1
147	High power blue□violet InGaN laser diodes grown on bulk GaN substrates by plasma-assisted molecular beam epitaxy. *Semiconductor Science and Technology*, **2005**, 20, 809-813	1.8	30
146	High mobility two-dimensional electron gas in AlGaN□GaN heterostructures grown on bulk GaN by plasma assisted molecular beam epitaxy. *Applied Physics Letters*, **2005**, 86, 102106	3.4	52
145	Resonant localized donor state above the conduction band minimum in InN. *Applied Physics Letters*, **2005**, 86, 262105	3.4	16

144	Fully-screened polarization-induced electric fields in blue□violet InGaN□GaN light-emitting devices grown on bulk GaN. *Applied Physics Letters*, **2005**, 87, 041109	3.4	37
143	Properties of violet laser diodes grown on bulk GaN substrates **2005**,		4
142	Growth of AlN, GaN and InN from the solution. *International Journal of Materials and Product Technology*, **2005**, 22, 226	1	19
141	Properties of InGaN blue laser diodes grown on bulk GaN substrates. *Journal of Crystal Growth*, **2005**, 281, 107-114	1.6	6
140	Spontaneous and stimulated emission in quantum structures grown over bulk GaN and sapphire. *Journal of Crystal Growth*, **2005**, 281, 183-187	1.6	2
139	Resonant shake-up satellites in photoemission at the Ga 3p photothreshold in GaN. *Solid State Communications*, **2005**, 136, 191-195	1.6	4
138	Microstructure of III-N semiconductors related to their applications in optoelectronics. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2005**, 2, 1366-1373		1
137	Modeling of elastic, piezoelectric and optical properties of vertically correlated GaN/AlN quantum dots. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2005**, 2, 972-975		2
136	Screening of built-in electric fields in group III-nitride laser diodes observed by means of hydrostatic pressure. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2005**, 2, 1019-1022		1
135	Enhancement of localization and confinement effects in quaternary group-III nitride multi-quantum wells on SiC substrate. *Physica Status Solidi (A) Applications and Materials Science*, **2005**, 202, 642-646	1.6	1
134	Localization Effects in InGaN/GaN Double Heterostructure Laser Diode Structures Grown on Bulk GaN Crystals. *Japanese Journal of Applied Physics*, **2005**, 44, 7244-7249	1.4	2
133	Efficient radiative recombination and potential profile fluctuations in low-dislocation InGaN□GaN multiple quantum wells on bulk GaN substrates. *Journal of Applied Physics*, **2005**, 97, 103507	2.5	20
132	Blue-violet InGaN laser diodes grown on bulk GaN substrates by plasma-assisted molecular-beam epitaxy. *Applied Physics Letters*, **2005**, 86, 011114	3.4	62
131	Free and bound excitons in GaN□AlGaN homoepitaxial quantum wells grown on bulk GaN substrate along the nonpolar (112□0) direction. *Applied Physics Letters*, **2005**, 86, 162112	3.4	25
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